



Driver circuit for Si photodiode array

C9004

Driver circuit for 16-element photodiode array

Features

- High precision and high-speed measurement by simultaneous 16-channel readout
- Assembled with pulse generator (8-step adjustable oscillatory frequency) CLK, START, A/D conversion Trig and EOS pulse output
- Choice of gain (conversion impedance): 1 × 10⁶ or 1 × 10⁷ (V/A)
- Hamamatsu S4111-16 series, S11212 series photodiode arrays are directly mountable on board.
- Single power supply operation: +12 V

Applications

Performance evaluation of Hamamatsu S4111-16 series, S11212 series photodiode arrays

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- Position measurement
- Displacement measurement

Absolute maximum ratings (Ta=25 °C unless otherwise noted)

Parameter	Symbol	Value	Unit
Supply voltage	Vcc max.	+18	V
Input current	Iin max.	+6.7 × 10 ⁻⁵	А
Operating temperature*1	Topr	0 to +50	°C
Storage temperature*1	Tstg	-20 to +80	°C

*1: No dew condensation

When there is a temperature difference between a product and the surrounding area in high humidity environment, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

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Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Input current range	Iin	$Tz=1 \times 10^{6}$	-	-	1×10^{-5}	A
		$Tz=1 \times 10^7$	-	-	1×10^{-6}	A
Conversion impedance*2	Tz		1×10^{6}	-	1×10^{7}	V/A
Output offset voltage	Vos	$Tz=1 \times 10^{6}$	-	0.025	-	V
		(set up prior to shipping)				
		$Tz=1 \times 10^{7 \times 3}$	-	0.25	-	V
Output amplitude voltage	Vo	Tz=1 \times 10 ⁶ , RL=1 k Ω	0	-	+10	V
		Tz=1 × 10 ⁷ , RL=1 k Ω	0	-	+10	V
Output noise voltage	enp-p	$Tz=1 \times 10^{6}$	-	5	-	mVp-p
		(full bandwidth)				
		$Tz=1 \times 10^7$	-	10	-	mVp-p
		(full bandwidth)				
Rise time	tr	Tz=1 × 10 ⁶ , RL=1 kΩ	-	5.6	-	μs
		$Tz=1 \times 10^7$, RL=1 k Ω	-	5.6	-	μs
Capacitive load	CL		-	-	100	pF
Oscillatory frequency (OUT)* ⁴	CLK		1.5625	-	200	kHz
Start pulse width (OUT)*4	-		5	-	640	μs
Output format*5	-			TTL		-
Current consumption	Icc		-	200	250	mA

Electrical and optical characteristics (Ta=25 °C)

*2: Conversion impedance can be changed with the switch on the circuit board.

*3: The variable resistor V_R on the circuit board must be used for making offset adjustments.

*4: Adjustable in 8 steps by using the BCD rotary switch on the circuit board

*5: CLK, START, Trig and EOS pulse output format

Block diagram





Driver circuit for Si photodiode array

Timing chart



Dimensional outline (unit: mm)



Tolerance unless otherwise noted $\leq 6 : \pm 0.1$ $6 < \leq 30: \pm 0.2$ $30 < : \pm 0.3$ KACCA0117EC



Connection example



Accessories

- · Instruction manual
- · AC adapter
- · Flat cable (200 mm) with I/O connector receptacle

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

- Precautions
- Disclaimer

Information described in this material is current as of July 2016.

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